

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	250/310,492.2,	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:17
L2	3676	((250/310,492.2,) or (382/145,149,)).CCLS.	USPAT	OR	OFF	2005/05/25 09:18
L3	5	2 and ( semiconductor near4 topology )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L4	162	2 and ( aspect near2 ratio )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L5	44	4 and ( contact near2 hole )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L6	71	4 and ( inspect near4 hole or defect )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L7	42	6 and ( electron near2 microscope )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:20
L8	39	7 and ( inspect\$3 near4 semiconductor or wafer )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21
L9	39	7 and ( topology near4 semiconductor or wafer )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21

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L10	58	6 and ( topology near4 semiconductor or wafer )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21
L11	2	6 and ( aspect adj ratio near4 value )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:22
L12	2	10 and ( aspect adj ratio near4 value )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
L13	1	7 and ( aspect adj ratio near4 value )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
L14	6	7 and ( aspect adj ratio near4 "1.5" )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
S1	457	Electron adj lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:41
S2	67199	Lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:41
S3	17257	S2 and ( electron near4 beam )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:42